

DFNWB2×2-6L-U Power Management Transistors- MOSFET

CJMNT32 PNP Power Transistor with N-MOSFET

DESCRIPTIONS

The CJMNT32 is PNP bipolar power transistor with 20V N-MOSFET. This device is suitable for use in charging circuit and other power management.

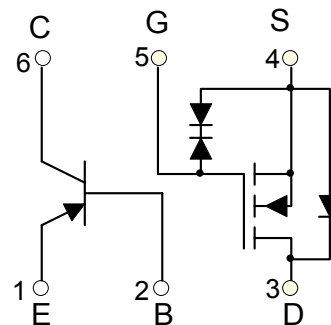
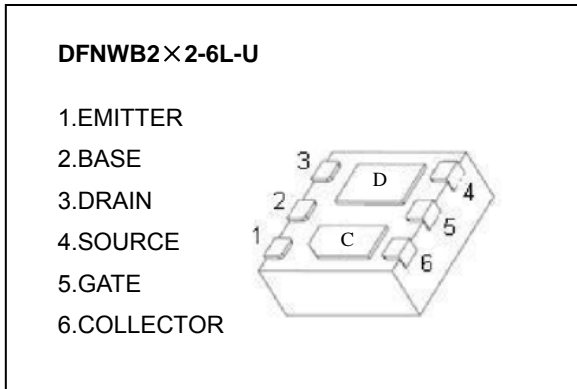
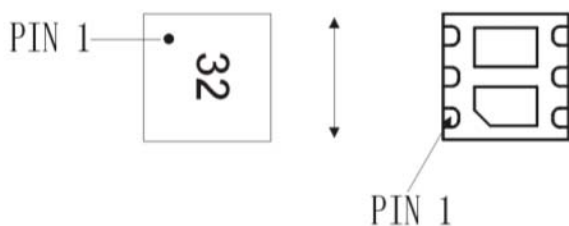
FEATURE

- Ultra low collector-to-emitter saturation voltage
- High DC current gain
- Small package DFNWB2×2-6L-U

APPLICATION

- Charging circuit
- Other power management in portable equipment

MARKING: 32



ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
PNP Transistor			
V _{CBO}	Collector-Base Voltage	-32	V
V _{CEO}	Collector-Emitter Voltage	-32	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current-Continuous(Note1)	-1.5	A
	Collector Current-Continuous(Note2)	-0.6	A
I _{CM}	Collector Current-Pulse(Note3)	-4	A
N-MOSFET			
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±5	V
I _D	Continuous Drain Current (note 1)	0.8	A
	Collector Current-Continuous(Note2)	0.69	A
I _{DM}	Collector Current-Pulse(Note3)	1.4	A

Temperature and Thermal Resistance			
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient (note 2)	178.6	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$
T_L	Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
PNP Transistor						
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-32			V
Collector-emitter breakdown	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-0.5\text{A}$	100		300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-0.5\text{A}, I_B=-50\text{mA}$			-0.35	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-0.5\text{A}, I_B=-50\text{mA}$			-1.5	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE}=-2\text{V}, I_C=-500\text{mA}$			-1.1	V
N-MOSFET						
STATIC PARAMETERS						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 16\text{V}, V_{GS} = 0\text{V}$			100	nA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 5\text{V}, V_{DS} = 0\text{V}$			± 1	μA
Gate threshold voltage (note 3)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.44		1.1	V
Drain-source on-resistance(note 3)	$R_{DS(on)}$	$V_{GS} = 4.5\text{V}, I_D = 0.55\text{A}$			600	m Ω
		$V_{GS} = 2.5\text{V}, I_D = 0.5\text{A}$			650	m Ω
		$V_{GS} = 1.8\text{V}, I_D = 0.35\text{A}$			700	m Ω
Diode forward voltage (note 3)	V_{SD}	$I_S = 0.35\text{A}, V_{GS} = 0\text{V}$	0.5		1.1	V
DYNAMIC PARAMETERS (note 4)						
Input Capacitance	C_{iss}	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}, f = 100\text{KHz}$		61		pF
Output Capacitance	C_{oss}			17		pF
Reverse Transfer Capacitance	C_{rss}			10		pF
SWITCHING PARAMETERS (note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{GEN} = 4.5\text{V}, V_{DD} = 10\text{V}, I_D = 500\text{mA}, R_{GEN} = 6\Omega, R_L = 10\Omega$		33		ns
Turn-on rise time	t_r			102		ns
Turn-off delay time	$t_{d(off)}$			790		ns
Turn-off fall time	t_f			439		ns
Total Gate Charge	Q_g	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V}, I_D = 0.6\text{A}$		1.15		nC
Gate-Source Charge	Q_{gs}			0.15		nC
Gate-Drain Charge	Q_{gd}			0.23		nC

Notes :

- 1.Surface mounted on FR4 board using 1 square inch pad size,1oz copper.
- 2.Surface mounted on FR4 board using the minimum pad size,1oz copper.
3. Pulse test : Pulse width=300 μs , duty cycle $\leq 2\%$.
4. These parameters have no way to verify.

Static Characteristic

